NPN Epitaxial Planar Silicon Transistor



2SC4390

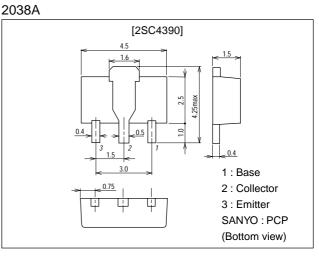
High-hFE, AF Amplifier Applications

Features

- · Adoption of MBIT process.
- \cdot High DC current gain (h_{FE}\!=\!800 to 3200).
- \cdot Large current capacity (I_C=2A).
- · Low collector-to-emitter saturation voltage $(V_{CE(sat)} \le 0.3V)$.
- · High V_{EBO} ($V_{EBO} \ge 15V$).

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		20	V
Collector-to-Emitter Voltage	VCEO		10	V
Emitter-to-Base Voltage	VEBO		15	V
Collector Current	۱ _C		2	Α
Collector Current (Pulse)	ICP		4	A
Base Current	Ι _Β		0.4	Α
Collector Dissipation	PC		500	mW
		Mounted on ceramic board (250mm ² ×0.8mm)	1.3	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	ICBO	V _{CB} =15V, I _E =0			0.1	μA
Emitter Cutoff Current	IEBO	V _{EB} =10V, I _C =0			0.1	μA
DC Current Gain	h _{FE} 1	$V_{CE}=2V, I_{C}=500$ mA	800	1500	3200	
	h _{FE} 2	V _{CE} =2V, I _C =2A	400			
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =50mA		260		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		28		рF

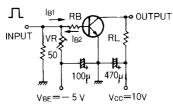
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Onit
Collector-to-Emitter Saturation Voltage	VCE(sat)	I _C =1A, I _B =20mA		0.11	0.5	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =1A, I _B =20mA		0.87	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =10μA, I _E =0	20			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =1mA, R _{BE} =∞	10			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =10μA, I _C =0	15			V
Turn-on Time	ton	See specified Test Circuit.		0.13		μs
Storage Time	^t stg	See specified Test Circuit.		0.8		μs
Fall Time	t _f	See specified Test Circuit.		0.1		μs

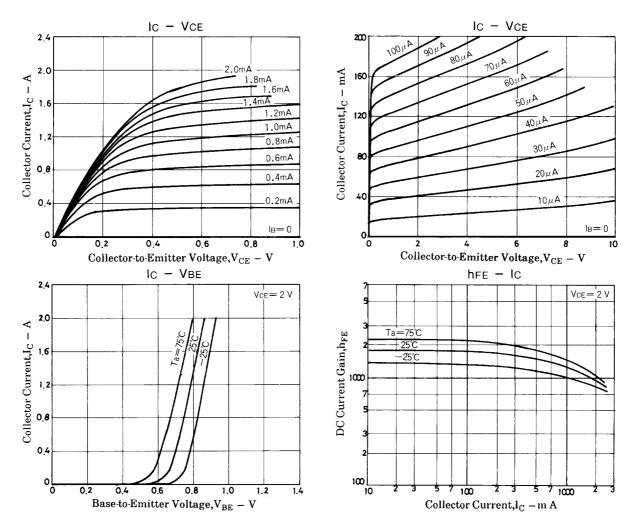
Switching Time Test Circuit

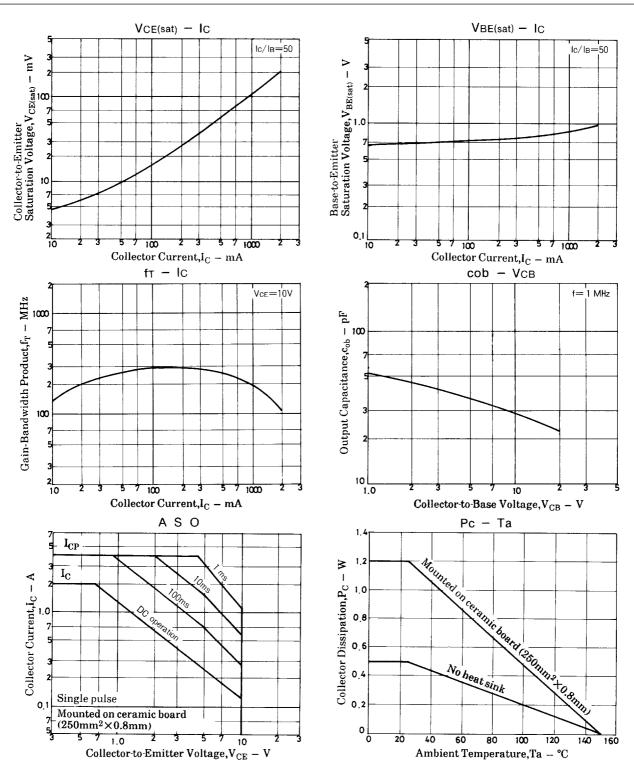
 $\begin{array}{c} PW \!=\! 20 \mu s \\ DC \!\leq\! 1\% \end{array}$



 $100I_{B1} = -100I_{B2} = I_C = 700 \text{mA}$

Unit (resistance : Ω , capacitance : F)





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